

BLS6G2731-120; BLS6G2731S-120

LDMOS S-band radar power transistor

Rev. 01 — 14 November 2008

Product data sheet

1. Product profile

1.1 General description

120 W LDMOS power transistor intended for radar applications in the 2.7 GHz to 3.1 GHz range.

Table 1. Typical performance

Typical RF performance at $T_{case} = 25\text{ }^{\circ}\text{C}$; $t_p = 100\text{ }\mu\text{s}$; $\delta = 10\text{ }\%$; $I_{Dq} = 100\text{ mA}$; in a class-AB production test circuit.

Mode of operation	f (GHz)	V _{DS} (V)	P _L (W)	G _p (dB)	η_D (%)	t _r (ns)	t _f (ns)
pulsed RF	2.7 to 3.1	32	120	13.5	48	20	6

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features

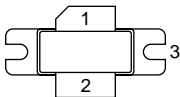
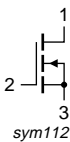
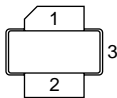
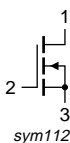
- Typical pulsed RF performance at a frequency of 2.7 GHz to 3.1 GHz, a supply voltage of 32 V, an I_{Dq} of 100 mA, a t_p of 100 μs with δ of 10 %:
 - ◆ Output power = 120 W
 - ◆ Power gain = 13.5 dB
 - ◆ Efficiency = 48 %
- Easy power control
- Integrated ESD protection
- High flexibility with respect to pulse formats
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (2.7 GHz to 3.1 GHz)
- Internally matched for ease of use
- Compliant to Directive 2002/95/EC, regarding restriction of hazardous substances (RoHS)

1.3 Applications

- S-band power amplifiers for radar applications in the 2.7 GHz to 3.1 GHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
BLS6G2731-120 (SOT502A)			
1	drain		 sym112
2	gate		
3	source		
BLS6G2731S-120 (SOT502B)			
1	drain		 sym112
2	gate		
3	source		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLS6G2731-120	-	flanged LDMOST ceramic package; 2 mounting holes; 2 leads	SOT502A
BLS6G2731S-120	-	earless flanged LDMOST ceramic package; 2 leads	SOT502B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Min	Max	Unit
V_{DS}	drain-source voltage	-	60	V
V_{GS}	gate-source voltage	-0.5	+13	V
I_D	drain current	-	33	A
T_{stg}	storage temperature	-65	+150	°C
T_j	junction temperature	-	225	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$Z_{th(j-mb)}$	transient thermal impedance from junction to mounting base	$T_{case} = 85\text{ °C}; P_L = 120\text{ W}$		
		$t_p = 100\text{ }\mu\text{s}; \delta = 10\text{ }\%$	0.23	K/W
		$t_p = 200\text{ }\mu\text{s}; \delta = 10\text{ }\%$	0.28	K/W
		$t_p = 300\text{ }\mu\text{s}; \delta = 10\text{ }\%$	0.32	K/W
		$t_p = 100\text{ }\mu\text{s}; \delta = 20\text{ }\%$	0.33	K/W

6. Characteristics

Table 6. Characteristics

$T_j = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}; I_D = 0.6\text{ mA}$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}; I_D = 180\text{ mA}$	1.4	1.8	2.4	V
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}; V_{DS} = 28\text{ V}$	-	-	4.2	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75\text{ V}; V_{DS} = 10\text{ V}$	27	33	-	A
I_{GSS}	gate leakage current	$V_{GS} = 11\text{ V}; V_{DS} = 0\text{ V}$	-	-	450	nA
g_{fs}	forward transconductance	$V_{DS} = 10\text{ V}; I_D = 9\text{ A}$	8.1	13	-	S
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75\text{ V}; I_D = 6.3\text{ A}$	-	0.085	0.135	Ω

7. Application information

Table 7. Application information

Mode of operation: pulsed RF; $t_p = 100\text{ }\mu\text{s}; \delta = 10\text{ }\%$; RF performance at $V_{DS} = 32\text{ V}; I_{Dq} = 100\text{ mA}; T_{case} = 25\text{ °C}$; unless otherwise specified, in a class-AB production circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
P_L	output power		-	120	-	W
V_{CC}	supply voltage	$P_L = 120\text{ W}$	-	-	32	V
G_p	power gain	$P_L = 120\text{ W}$	12	13.5	-	dB
RL_{in}	input return loss	$P_L = 120\text{ W}$	-	7	-	dB
$P_{L(1dB)}$	output power at 1 dB gain compression		-	130	-	W
η_D	drain efficiency	$P_L = 120\text{ W}$	40	48	-	%
$P_{droop(pulse)}$	pulse droop power	$P_L = 120\text{ W}$	-	0	0.5	dB
t_r	rise time	$P_L = 120\text{ W}$	-	20	50	ns
t_f	fall time	$P_L = 120\text{ W}$	-	6	50	ns

Table 8. Typical impedance

f GHz	Z _S Ω	Z _L Ω
2.7	3.4 – j7.2	4.6 – j4.4
2.8	3.8 – j5.9	3.8 – j4.6
2.9	4.7 – j4.8	3.0 – j4.6
3.0	6.3 – j4.1	2.3 – j4.3
3.1	8.8 – j4.9	1.8 – j3.9

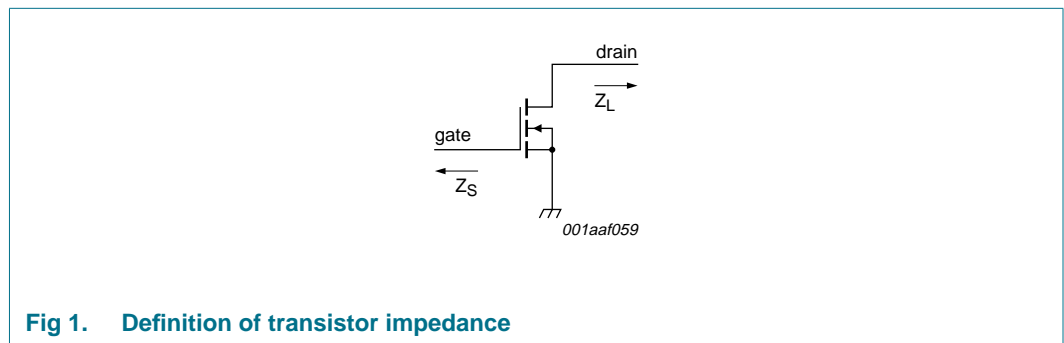
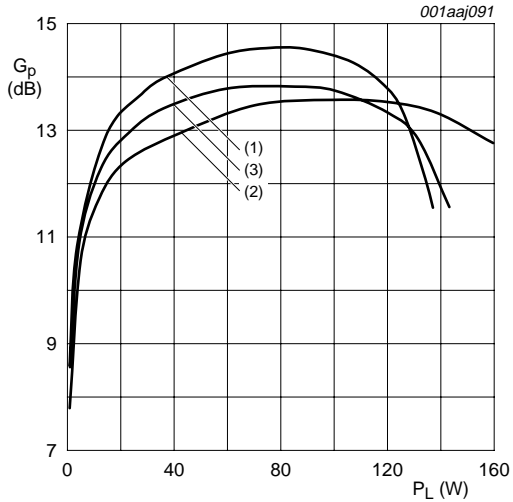


Fig 1. Definition of transistor impedance

7.1 Ruggedness in class-AB operation

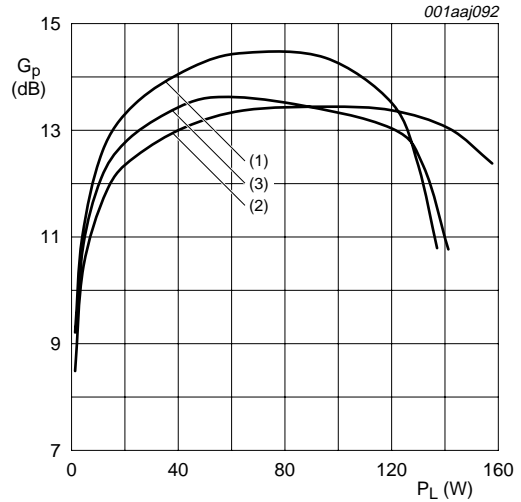
The BLS6G2731-120 and BLS6G2731S-120 are capable of withstanding a load mismatch corresponding to VSWR = 5 : 1 through all phases under the following conditions: $V_{DS} = 32\text{ V}$; $I_{Dq} = 100\text{ mA}$; $P_L = 120\text{ W}$; $t_p = 100\text{ }\mu\text{s}$; $\delta = 10\text{ \%}$.

7.2 Graphs



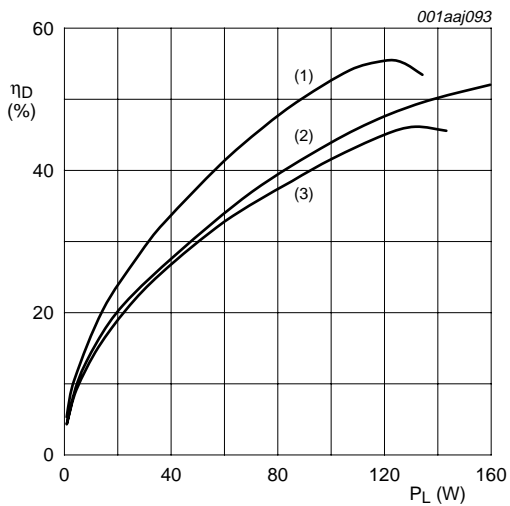
$V_{DS} = 32\text{ V}; I_{Dq} = 100\text{ mA}; t_p = 300\text{ }\mu\text{s}; \delta = 10\text{ }\%$.
 (1) $f = 2.7\text{ GHz}$
 (2) $f = 2.9\text{ GHz}$
 (3) $f = 3.1\text{ GHz}$

Fig 2. Power gain as a function of load power; typical values



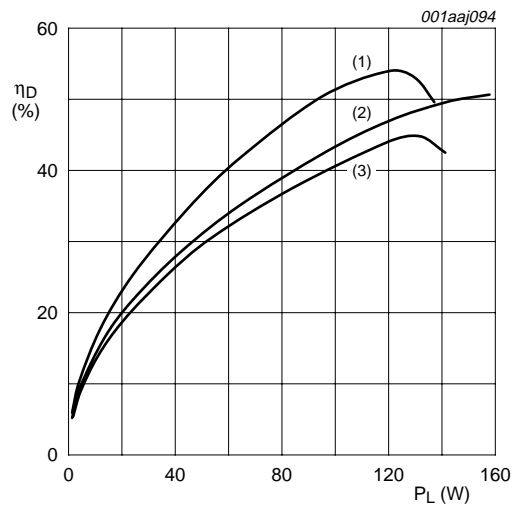
$V_{DS} = 32\text{ V}; I_{Dq} = 100\text{ mA}; t_p = 100\text{ }\mu\text{s}; \delta = 20\text{ }\%$.
 (1) $f = 2.7\text{ GHz}$
 (2) $f = 2.9\text{ GHz}$
 (3) $f = 3.1\text{ GHz}$

Fig 3. Power gain as a function of load power; typical values



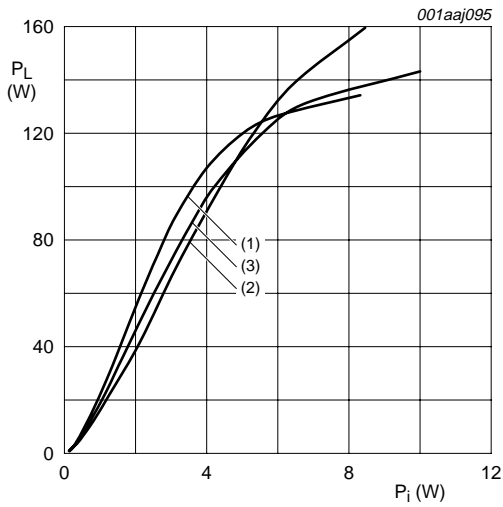
$V_{DS} = 32\text{ V}; I_{Dq} = 100\text{ mA}; t_p = 300\text{ }\mu\text{s}; \delta = 10\text{ }\%$.
 (1) $f = 2.7\text{ GHz}$
 (2) $f = 2.9\text{ GHz}$
 (3) $f = 3.1\text{ GHz}$

Fig 4. Drain efficiency as a function of load power; typical values



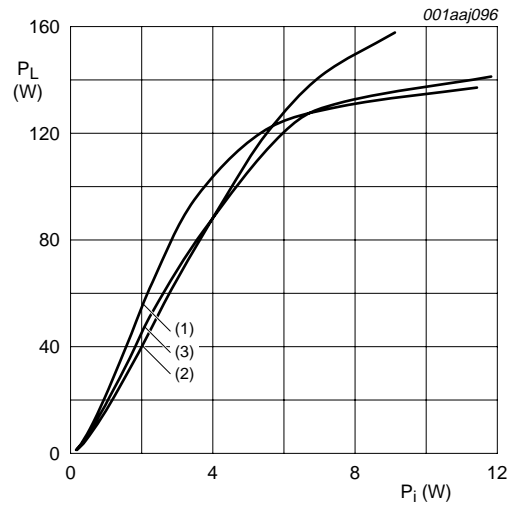
$V_{DS} = 32\text{ V}; I_{Dq} = 100\text{ mA}; t_p = 100\text{ }\mu\text{s}; \delta = 20\text{ }\%$.
 (1) $f = 2.7\text{ GHz}$
 (2) $f = 2.9\text{ GHz}$
 (3) $f = 3.1\text{ GHz}$

Fig 5. Drain efficiency as a function of load power; typical values



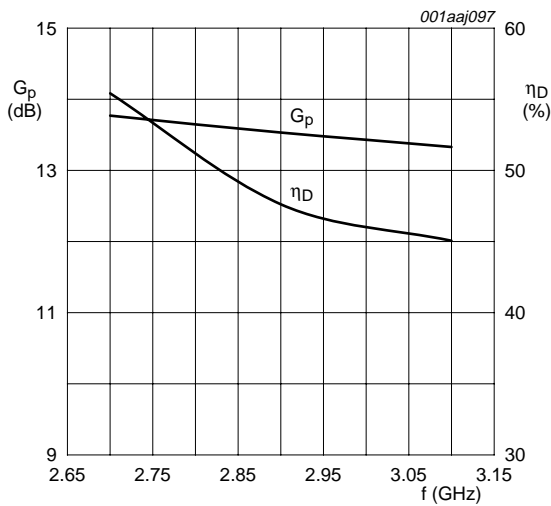
$V_{DS} = 32\text{ V}; I_{DQ} = 100\text{ mA}; t_p = 300\text{ }\mu\text{s}; \delta = 10\text{ }\%$.
 (1) $f = 2.7\text{ GHz}$
 (2) $f = 2.9\text{ GHz}$
 (3) $f = 3.1\text{ GHz}$

Fig 6. Load power as a function of input power; typical values



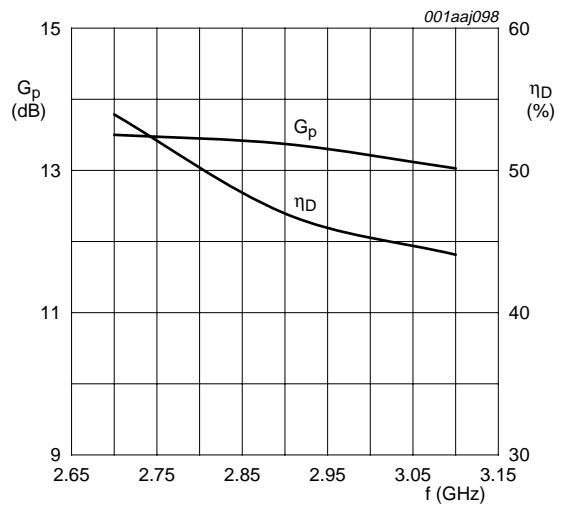
$V_{DS} = 32\text{ V}; I_{DQ} = 100\text{ mA}; t_p = 100\text{ }\mu\text{s}; \delta = 20\text{ }\%$.
 (1) $f = 2.7\text{ GHz}$
 (2) $f = 2.9\text{ GHz}$
 (3) $f = 3.1\text{ GHz}$

Fig 7. Load power as a function of input power; typical values



$P_L = 120\text{ W}; V_{DS} = 32\text{ V}; I_{DQ} = 100\text{ mA}; t_p = 300\text{ }\mu\text{s}; \delta = 10\text{ }\%$.

Fig 8. Power gain and drain efficiency as function of frequency; typical values



$P_L = 120\text{ W}; V_{DS} = 32\text{ V}; I_{DQ} = 100\text{ mA}; t_p = 100\text{ }\mu\text{s}; \delta = 20\text{ }\%$.

Fig 9. Power gain and drain efficiency as function of frequency; typical values

8. Test information

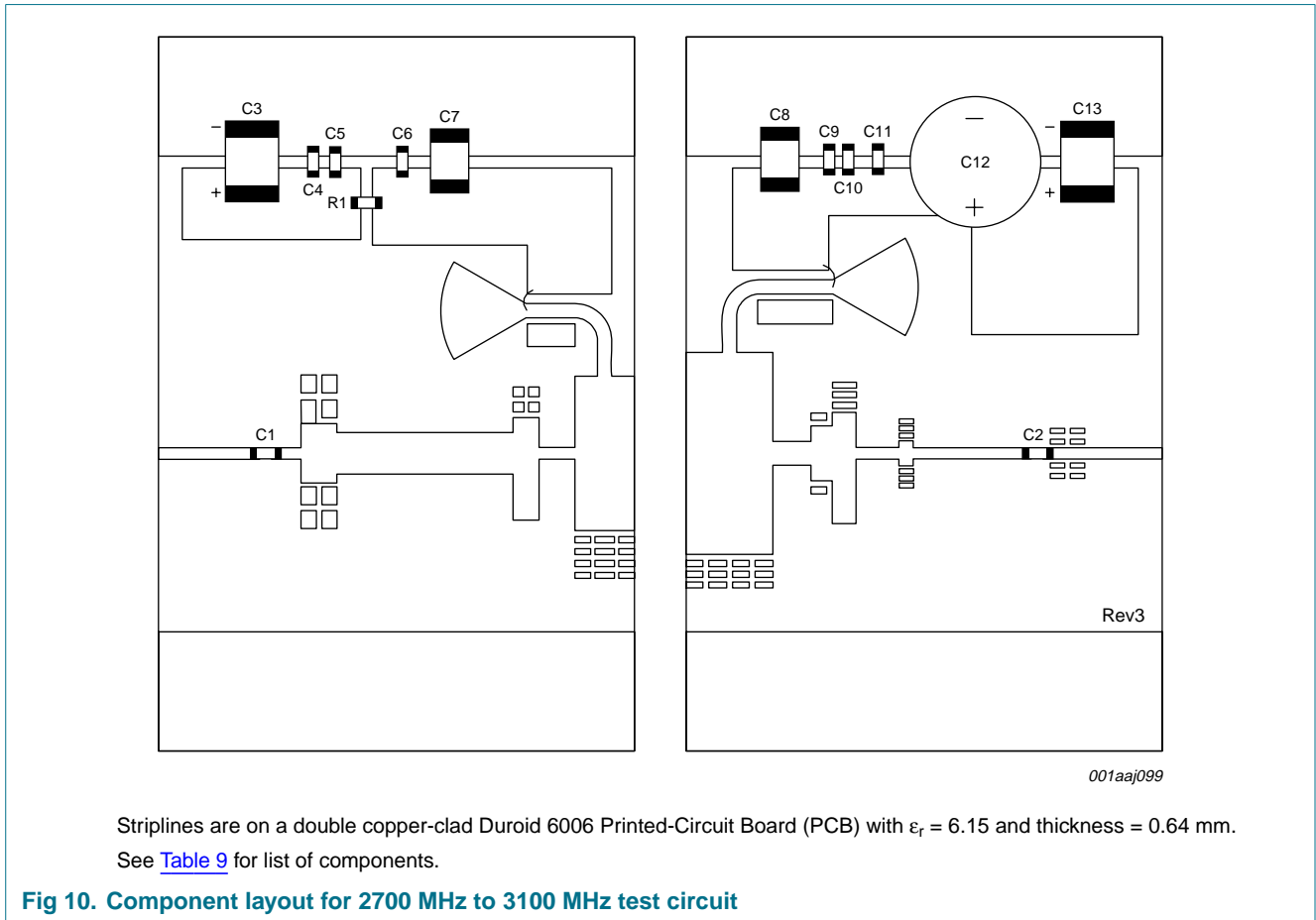


Table 9. List of components

See [Figure 10](#).

Component	Description	Value	Remarks
C1, C2	multilayer ceramic chip capacitor	24 pF	ATC 100A or equivalent
C3	multilayer ceramic chip capacitor	47 μ F; 20 V	
C4, C6, C9, C10	multilayer ceramic chip capacitor	33 pF	ATC 100A or equivalent
C5, C11	multilayer ceramic chip capacitor	1 nF	ATC 100A or equivalent
C7, C8	multilayer ceramic chip capacitor	100 pF	ATC 100B or equivalent
C12	electrolytic capacitor	47 μ F; 63 V	
C13	multilayer ceramic chip capacitor	10 μ F; 35 V	
R1	SMD resistor	56 Ω	SMD 0603

9. Package outline

Flanged LDMOST ceramic package; 2 mounting holes; 2 leads

SOT502A

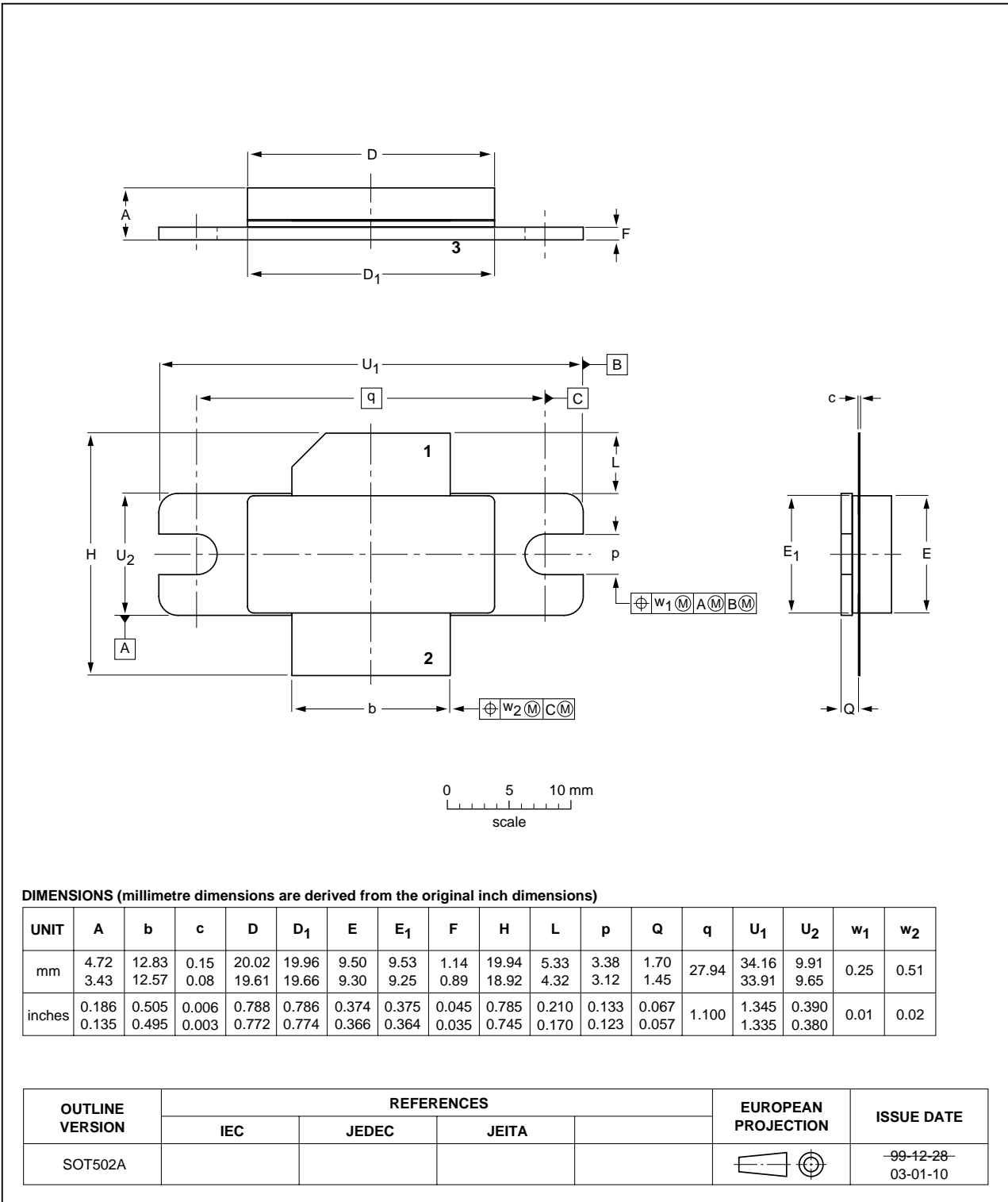


Fig 11. Package outline SOT502A

Earless flanged LDMOST ceramic package; 2 leads

SOT502B

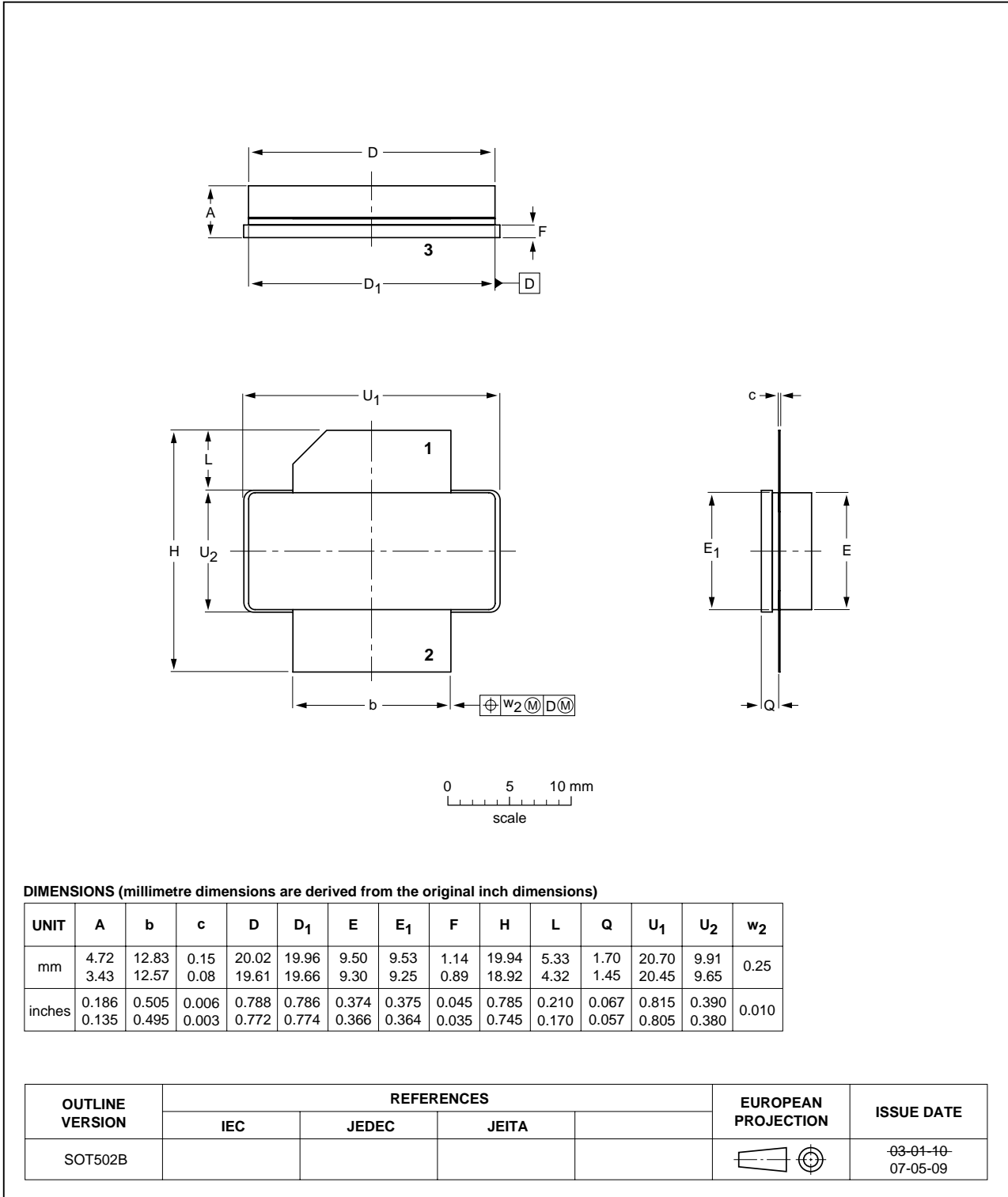


Fig 12. Package outline SOT502B

10. Abbreviations

Table 10. Abbreviations

Acronym	Description
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LDMOST	Laterally Diffused Metal-Oxide Semiconductor Transistor
RF	Radio Frequency
S-band	Short wave Band
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLS6G2731-120_6G2731S-120_1	20081114	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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14. Contents

1	Product profile	1
1.1	General description	1
1.2	Features	1
1.3	Applications	2
2	Pinning information	2
3	Ordering information	2
4	Limiting values	2
5	Thermal characteristics	3
6	Characteristics	3
7	Application information	3
7.1	Ruggedness in class-AB operation	4
7.2	Graphs	5
8	Test information	7
9	Package outline	8
10	Abbreviations	10
11	Revision history	10
12	Legal information	11
12.1	Data sheet status	11
12.2	Definitions	11
12.3	Disclaimers	11
12.4	Trademarks	11
13	Contact information	11
14	Contents	12



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